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Vishay Semiconductor/Diodes Division VS-10WT10FNTR

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### VS-10UT10, VS-10WT10FN

Vishay Semiconductors

## High Performance Generation 5.0 Schottky Rectifier, 10 A





Base

cathode 9 4

I-PAK (TO-251AA) D-PAK (TO-252AA) Base cathode 4 3 Anode Anode Anode 75 Cathode

Anode

75

3

1 Cathode

**VS-10UT10** 

VS-10WT10FN

PRODUCT SUMMARY				
Package	I-PAK (TO-251AA), D-PAK (TO-252AA)			
I <sub>F(AV)</sub>	10 A			
V <sub>R</sub>	100 V			
$V_F$ at $I_F$	0.66 V			
I <sub>RM</sub> max.	4 mA at 125 °C			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			
E <sub>AS</sub>	54 mJ			

#### **FEATURES**

- 175 °C high performance Schottky diode
- Very low forward voltage drop
- Extremely low reverse leakage
- RoHS Optimized V<sub>F</sub> vs. I<sub>R</sub> trade off for high efficiency COMPLIANT
- · Increased ruggedness for reverse avalanche capability
- RBSOA available
- Negligible switching losses
- Submicron trench technology
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47

#### APPLICATIONS

- High efficiency SMPS
- High frequency switching
- Output rectification
- Reverse battery protection
- Freewheeling
- DC/DC systems
- · Increased power density systems

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
V <sub>RRM</sub>		100	V			
VF	10 Apk, $T_J = 125 \ ^\circ C$ (typical)	0.615	V			
TJ	Range	- 55 to 175	۵°			

VOLTAGE RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VS-10UT10 VS-10WT10FN	UNITS
Maximum DC reverse voltage	V <sub>R</sub>	T <sub>J</sub> = 25 °C	100	V

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	I <sub>F(AV)</sub>	50 % duty cycle at $T_C$ = 159 °C, rectangular waveform		10	А
Maximum peak one cycle non-repetitive surge current	I <sub>FSM</sub>	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated V <sub>RRM</sub> applied <sup>(1)</sup>	610	A
		10 ms sine or 6 ms rect. pulse		110	
Non-repetitive avalanche energy	E <sub>AS</sub>	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 3 A, L = 12 mH		54	mJ
Repetitive avalanche current	I <sub>AR</sub>	Limited by frequency of operation and time pulse duration so that $T_J < T_J$ max. $I_{AS}$ at $T_J$ max. as a function of time pulse (see fig. 8)		I <sub>AS</sub> at T <sub>J</sub> max.	A

#### Note

<sup>(1)</sup> Measured connecting 2 anode pins

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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Forward voltage drop		5 A	T <sub>J</sub> = 25 °C	0.630	-	- V
		10 A		0.735	0.810	
	V <sub>FM</sub> <sup>(1)(2)</sup>	20 A		0.840	0.890	
		5 A	T <sub>J</sub> = 125 °C	0.530	-	
		10 A		0.615	0.660	
		20 A		0.730	0.770	
Reverse leakage current	I <sub>RM</sub> <sup>(1)</sup>	T <sub>J</sub> = 25 °C	V <sub>R</sub> = Rated V <sub>R</sub>	-	50	μA
		T <sub>J</sub> = 125 °C		-	4	mA
Junction capacitance	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		400	-	pF
Series inductance	Ls	Measured lead to lead 5 mm from package body		8.0	-	nH
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>		-	10 000	V/µs

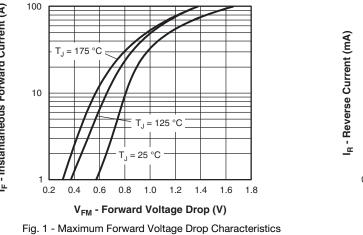
#### Notes

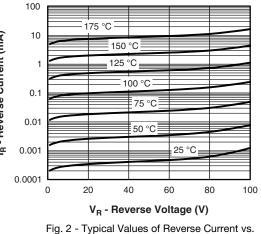
<sup>(1)</sup> Pulse width < 300  $\mu$ s, duty cycle < 2 %

<sup>(2)</sup> Only 1 anode pin connected

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 175	°C
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	2	°C/W
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>		0.3	0/10
A navevine ste vusiskt			0.3	g
Approximate weight			0.01	oz.
		Case style I-PAK	10U	T10
Marking device		Case style D-PAK	10WT	10FN







**Reverse Voltage** 

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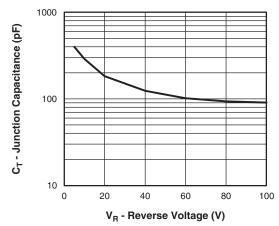


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

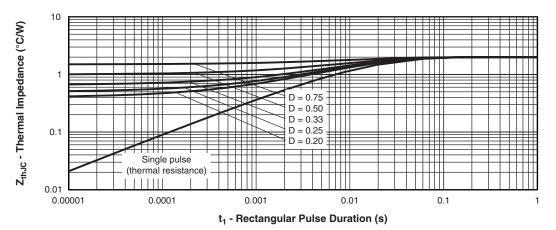
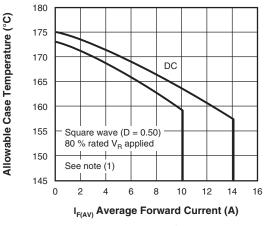
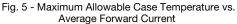


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

Average Power Loss (W)





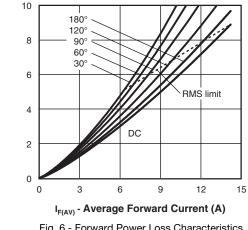


Fig. 6 - Forward Power Loss Characteristics

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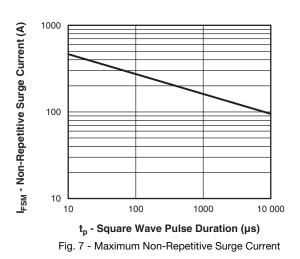




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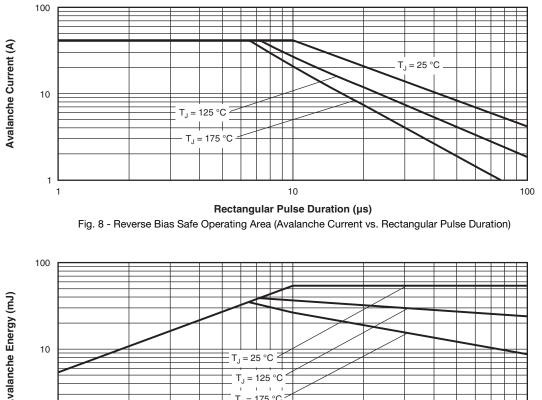
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#### Note

(1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 



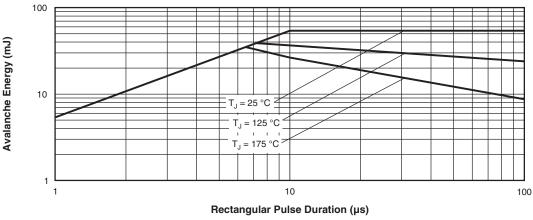


Fig. 9 - Reverse Bias Safe Operating Area (Avalanche Energy vs. Rectangular Pulse Duration)

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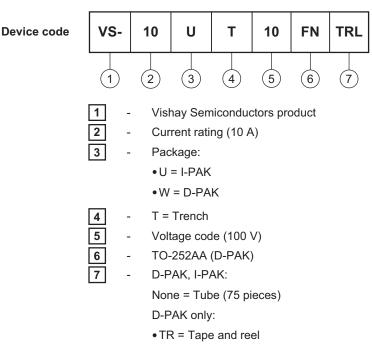


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#### ORDERING INFORMATION TABLE



- TRL = Tape and reel (left oriented)
- TRR = Tape and reel (right oriented)

LINKS TO RELATED DOCUMENTS					
Dimensions	I-PAK (TO-251AA)	www.vishay.com/doc?95024			
Dimensions	D-PAK (TO-252AA)	www.vishay.com/doc?95448			
Part marking information	I-PAK (TO-251AA)	www.vishay.com/doc?95025			
	D-PAK (TO-252AA)	www.vishay.com/doc?95059			
Packaging information		www.vishay.com/doc?95033			
SPICE model		www.vishay.com/doc?95026			

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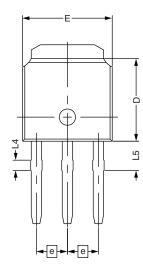


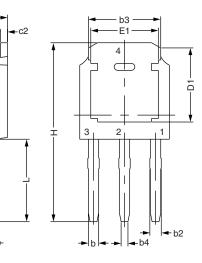
### **Outline Dimensions**

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I-PAK - S

#### DIMENSIONS FOR I-PAK - S in millimeters





SYMBOL	DIMENSIONAL REQUIREMENTS				
STMBOL	MIN.	NOM.	MAX.		
E	6.40	6.60	6.70		
L	3.98	4.13	4.28		
L4	0.66	0.76	0.86		
L5	1.96	2.16	2.36		
D	6.00	6.10	6.20		
Н	11.05	11.25	11.45		
b	0.64	0.76	0.88		
b2	0.77	0.84	1.14		
b3	5.21	5.34	5.46		
b4	0.41	0.51	0.61		
e	2.286 BSC				
A	2.20	2.30	2.38		
С	0.40	0.50	0.60		
c2	0.40	0.50	0.60		
D1	5.30	-	-		
E1	4.40	-	-		

с

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